Determine the number of quantum states N in Silicon between E_c and $E_c+0.05~{
m eV}$ at $T=300~{
m K}.$

Given:

- Effective mass of electrons: $m_n^st = 1.08 m_0$
- Planck's constant: $h=6.626 imes 10^{-34} \ \mathrm{J} \backslash \mathrm{cdotps}$
- ullet Thermal energy: $kT=0.02585~{
 m eV}$ (converted to Joules)

Solution:

1. Convert Thermal Energy kT to Joules:

$$kT = 0.02585 \text{ eV} \times 1.602 \times 10^{-19} \text{ J/eV} = 4.14 \times 10^{-21} \text{ J}$$

2. Density of States Function $g_c(E)$:

The density of states $g_c(E)$ for conduction band electrons is given by:

$$g_c(E \geq E_c) = rac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c}$$

3. Integral to Find Number of States N:

To find the number of states between E_c and $E_c+0.05~{\rm eV}$, integrate $g_c(E)$ from E_c to $E_c+0.05~{\rm eV}$:

$$N = \int_{E_c}^{E_c + 0.05 \; \mathrm{eV}} g_c(E) \, dE$$

4. Substitute the Expression for $g_c(E)$:

$$N = \int_{E_c}^{E_c + 0.05 \, {
m eV}} rac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c} \, dE$$

5. Change of Variables:

Let $x=E-E_c$ so dE=dx. The limits of integration become 0 to 0.05 eV:

$$N = rac{4\pi (2m_n^*)^{3/2}}{h^3} \int_0^{0.05\,{
m eV}} \sqrt{x}\,dx$$

6. Evaluate the Integral:

The integral of \sqrt{x} with respect to x is:

$$\int_0^{0.05\,\mathrm{eV}} \sqrt{x}\,dx = rac{2}{3}x^{3/2}igg|_0^{0.05\,\mathrm{eV}}$$
 $\int_0^{0.05\,\mathrm{eV}} \sqrt{x}\,dx = rac{2}{3}(0.05)^{3/2}$ $(0.05)^{3/2} = 0.00052\,\mathrm{eV}^{3/2}$ $\int_0^{0.05\,\mathrm{eV}} \sqrt{x}\,dx pprox rac{2}{3} imes 0.00052 = 0.00034\,\mathrm{eV}^{3/2}$

- 7. Substitute and Calculate N:
 - Convert Planck's constant h to J\cdotps:

$$h^3 = (6.626 \times 10^{-34} \text{ J} \cdot \text{cdotp})^3 = 2.93 \times 10^{-101} \text{ J}^3 \cdot \text{cdotps}^3$$

7. Substitute and Calculate N:

Convert Planck's constant h to J\cdotps:

$$h^3 = (6.626 \times 10^{-34} \text{ J} \cdot \text{cdotps})^3 = 2.93 \times 10^{-101} \text{ J}^3 \cdot \text{cdotps}^3$$

· Effective mass factor:

$$(2m_n^*)^{3/2} = (2 imes 1.08 imes 9.11 imes 10^{-31})^{3/2} pprox 2.71 imes 10^{-45} \ \mathrm{kg}^{3/2}$$

• Combine these to find $\frac{(2m_n^*)^{3/2}}{h^3}$:

$$rac{(2m_n^*)^{3/2}}{h^3} = rac{2.71 imes 10^{-45}}{2.93 imes 10^{-101}} pprox 9.25 imes 10^{55} ext{ J}^{-3} \cdot{cdotps}^{-3}$$

· Combine with the integral result:

$$N = 9.25 \times 10^{55} \times 0.00034 = 3.15 \times 10^{52} \, \mathrm{states/cm}^3$$

Conclusion:

The number of quantum states in Silicon between E_c and $E_c+0.05~{\rm eV}$ at $T=300~{\rm K}$ is approximately $3.15\times 10^{52}~{\rm states/cm^3}$.

Problem:

Determine the number of quantum states N_c in the conduction band and N_v in the valence band of Silicon between given energy levels.

Given:

- Effective mass of electrons in the conduction band: $m_n^st=1.08m_0$
- Effective mass of holes in the valence band: $m_p^st=0.81m_0$
- Planck's constant: $h=6.626 imes 10^{-34}~\mathrm{J.s}$
- Thermal energy: $kT=0.02585~{
 m eV}$
- ullet Energy range for conduction band: from E_c to $E_c+0.05~{
 m eV}$
- ullet Energy range for valence band: from $E_v-0.05~{
 m eV}$ to E_v

Solution:

1. Convert Thermal Energy kT to Joules:

$$kT = 0.02585 \text{ eV} \times 1.602 \times 10^{-19} \text{ J/eV} = 4.14 \times 10^{-21} \text{ J}$$

2. Density of States Function in the Conduction Band $g_c(E)$:

The density of states $g_c(E)$ for conduction band electrons is given by:

$$g_c(E \geq E_c) = rac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c}$$

3. Density of States Function in the Valence Band $g_v(E)$:

The density of states $g_v(E)$ for valence band holes is given by:

$$g_v(E \leq E_v) = rac{4\pi (2m_p^*)^{3/2}}{h^3} \sqrt{E_v - E}$$

- 4. Integrals to Find Number of States N_c and N_v :
 - ullet For the conduction band (from E_c to $E_c+0.05~{
 m eV}$):

$$N_c = \int_{E_c}^{E_c+0.05~{
m eV}} g_c(E)\,dE$$

• For the valence band (from $E_v-0.05~{
m eV}$ to E_v):

$$N_v = \int_{E=-0.05~
m eV}^{E_v} g_v(E)\,dE$$

- 5. Substitute the Expression for $g_c(E)$ and $g_v(E)$:
 - · For the conduction band:

$$N_c = \int_{E_c}^{E_c + 0.05 \, {
m eV}} rac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c} \, dE$$

· For the valence band:

$$N_v = \int_{E_v = 0.05 \; {
m eV}}^{E_v} rac{4\pi (2m_p^*)^{3/2}}{h^3} \sqrt{E_v - E} \, dE$$

- 6. Change of Variables and Evaluate the Integrals:
 - Conduction Band:

Let $x=E-E_{c}$, so dE=dx. The limits become 0 to 0.05 eV:

$$N_c = rac{4\pi (2m_n^*)^{3/2}}{h^3} \int_0^{0.05\,{
m eV}} \sqrt{x}\,dx$$

Evaluate the integral:

$$\int_0^{0.05\,\mathrm{eV}} \sqrt{x}\,dx = rac{2}{3}x^{3/2}igg|_0^{0.05}$$
 $(0.05)^{3/2} = 0.00052$ $\int_0^{0.05\,\mathrm{eV}} \sqrt{x}\,dx pprox rac{2}{3} imes 0.00052 = 0.00034$

Valence Band:

Let $x=E_v-E$, so dE=-dx . The limits become 0 to 0.05 eV:

$$N_v = rac{4\pi (2m_p^*)^{3/2}}{h^3} \int_0^{0.05 \; {
m eV}} \sqrt{x} \, dx$$

The integral is the same as for the conduction band:

$$\int_{0}^{0.05 \text{ eV}} \sqrt{x} \, dx = 0.00034$$

Substitute and Calculate N_c and N_v :

Convert Planck's constant h to J.s:

$$h^3 = (6.626 \times 10^{-34} \text{ J.s})^3 = 2.93 \times 10^{-101} \text{ J}^3.\text{s}^3$$

· Effective mass factor for conduction band:

$$(2m_n^*)^{3/2} = (2 imes 1.08 imes 9.11 imes 10^{-31})^{3/2} pprox 2.71 imes 10^{-45} \ {
m kg}^{3/2}$$

Effective mass factor for valence band:

$$(2m_p^*)^{3/2} = (2 imes 0.81 imes 9.11 imes 10^{-31})^{3/2} pprox 2.04 imes 10^{-45} ext{ kg}^{3/2}$$

• Combine to find $\frac{(2m_n^*)^{3/2}}{h^3}$ and $\frac{(2m_p^*)^{3/2}}{h^3}$:

$$\frac{(2m_n^*)^{3/2}}{h^3} = \frac{2.71 \times 10^{-45}}{2.93 \times 10^{-101}} \approx 9.25 \times 10^{55} \,\mathrm{J}^{-3}.\mathrm{s}^{-3}$$

$$\frac{(2m_p^*)^{3/2}}{h^3} = \frac{2.04 \times 10^{-45}}{2.93 \times 10^{-101}} \approx 6.95 \times 10^{55} \,\mathrm{J}^{-3}.\mathrm{s}^{-3}$$

· Combine with the integral results:

$$N_c = 9.25 \times 10^{55} \times 0.00034 = 3.15 \times 10^{52} \, \mathrm{states/cm}^3$$

$$N_v = 6.95 \times 10^{55} \times 0.00034 = 2.36 \times 10^{52} \mathrm{\ states/cm}^3$$

Conclusion:

- The number of quantum states in the conduction band of Silicon between E_c and $E_c+0.05~{\rm eV}$ is approximately $3.15\times10^{52}~{\rm states/cm}^3$.
- The number of quantum states in the valence band of Silicon between $E_v-0.05~{\rm eV}$ and E_v is approximately $2.36\times 10^{52}~{\rm states/cm}^3$.

This revised solution uses the period (.) for multiplication and provides clear calculations for both the conduction and valence bands.

Problem Statement

In a silicon semiconductor, determine the number of available quantum states in the conduction band and valence band within specific energy ranges.

Given:

- Effective Mass of Electrons (Conduction Band): $m_n^* = 1.08m_0$, where m_0 is the free electron mass.
- Effective Mass of Holes (Valence Band): $m_p^* = 0.81 m_0$.
- Planck's Constant: $h=6.626 imes 10^{-34} ext{ J.s.}$
- Thermal Energy at Room Temperature (300 K): $kT=0.02585~{
 m eV}.$
- Energy Range for Conduction Band: From E_c to $E_c + 0.05 \; \mathrm{eV}$.
- Energy Range for Valence Band: From $E_v 0.05 \; \mathrm{eV}$ to E_v .

Task:

- 1. Calculate the number of quantum states N_c in the conduction band between E_c and $E_c+0.05~{\rm eV}.$
- 2. Calculate the number of quantum states N_v in the valence band between $E_v-0.05~{
 m eV}$ and E_v .

Solution

1. Number of Quantum States in the Conduction Band (N_c)

To find N_c , integrate the density of states function $g_c(E)$ over the given energy range. The density of states for the conduction band is:

$$g_c(E \geq E_c) = rac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c}$$

Integrate this from E_c to $E_c + 0.05 \text{ eV}$:

$$N_c = \int_{E_c}^{E_c+0.05~{
m eV}} g_c(E)\,dE$$

Substitute $g_c(E)$:

$$N_c = \int_{E_c}^{E_c + 0.05 \, \mathrm{eV}} rac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c} \, dE$$

Change the variable $x=E-E_{c}$, so dE=dx:

$$N_c = rac{4\pi (2m_n^*)^{3/2}}{h^3} \int_0^{0.05 \; {
m eV}} \sqrt{x} \, dx$$

Evaluate the integral:

$$\int_0^{0.05 \, \mathrm{eV}} \sqrt{x} \, dx = \frac{2}{3} x^{3/2} igg|_0^{0.05} = \frac{2}{3} imes (0.05)^{3/2}$$
 $(0.05)^{3/2} pprox 0.00052$ $\frac{2}{3} imes 0.00052 = 0.00034 \, \mathrm{eV}$

Thus:

$$N_c = \frac{4\pi (2m_n^*)^{3/2}}{h^3} \times 0.00034$$

2. Number of Quantum States in the Valence Band (N_v)

To find N_v , integrate the density of states function $g_v(E)$ over the specified energy range. The density of states for the valence band is:

$$g_v(E \leq E_v) = rac{4\pi (2m_p^*)^{3/2}}{h^3} \sqrt{E_v - E}$$

Integrate this from $E_v - 0.05 \text{ eV}$ to E_v :

$$N_v = \int_{E=0.05~eV}^{E_v} g_v(E) \, dE$$

Substitute $g_v(E)$:

$$N_v = \int_{E_v - 0.05 \; \mathrm{eV}}^{E_v} rac{4\pi (2m_p^*)^{3/2}}{h^3} \sqrt{E_v - E} \, dE$$

Change the variable $x=E_v-E$, so dE=-dx:

$$N_v = rac{4\pi (2m_p^*)^{3/2}}{h^3} \int_0^{0.05\,\mathrm{eV}} \sqrt{x}\,dx$$
 The integral result is the corner

The integral result is the same:

$$\int_0^{0.05\,{
m eV}} \sqrt{x}\,dx = 0.00034~{
m eV}$$

Thus:

$$N_v = rac{4\pi (2m_p^*)^{3/2}}{h^3} imes 0.00034$$

3. Substitute Values and Compute

Convert Planck's constant h to J.s:

$$h^3 = (6.626 \times 10^{-34} \text{ J.s})^3 = 2.93 \times 10^{-101} \text{ J}^3.\text{s}^3$$

Effective mass factor for conduction band:

$$(2m_n^*)^{3/2} = (2 \times 1.08 \times 9.11 \times 10^{-31})^{3/2} \approx 2.71 \times 10^{-45} \text{ kg}^{3/2}$$

Effective mass factor for valence band:

$$(2m_p^*)^{3/2} = (2 \times 0.81 \times 9.11 \times 10^{-31})^{3/2} \approx 2.04 \times 10^{-45} \text{ kg}^{3/2}$$

Calculate $\frac{(2m_n^*)^{3/2}}{h^3}$ and $\frac{(2m_p^*)^{3/2}}{h^3}$:

$$rac{(2m_n^*)^{3/2}}{h^3} = rac{2.71 imes 10^{-45}}{2.93 imes 10^{-101}} pprox 9.25 imes 10^{55} \,\mathrm{J}^{-3}.\mathrm{s}^{-3}$$
 $rac{(2m_p^*)^{3/2}}{h^3} = rac{2.04 imes 10^{-45}}{2.93 imes 10^{-101}} pprox 6.95 imes 10^{55} \,\mathrm{J}^{-3}.\mathrm{s}^{-3}$

Finally, the number of quantum states:

$$N_c = 9.25 \times 10^{55} \times 0.00034 = 3.15 \times 10^{52} \, \mathrm{states/cm}^3$$
 $N_v = 6.95 \times 10^{55} \times 0.00034 = 2.36 \times 10^{52} \, \mathrm{states/cm}^3$

Conclusion

- The number of quantum states in the conduction band of Silicon between E_c and $E_c+0.05~{\rm eV}$ is approximately $3.15\times10^{52}~{\rm states/cm}^3$.
- The number of quantum states in the valence band of Silicon between $E_v-0.05~{
 m eV}$ and E_v is approximately $2.36 imes 10^{52}~{
 m states/cm}^3$.

Determine the number of quantum states N_c in the conduction band and N_v in the valence band of Silicon between given energy levels. Use different energy ranges for these calculations.

Given:

- Effective Mass of Electrons (Conduction Band): $m_n^st = 1.08 m_0$
- Effective Mass of Holes (Valence Band): $m_p^st = 0.81 m_0$
- ullet Planck's Constant: $h=6.626 imes10^{-34}~\mathrm{J.s}$
- Thermal Energy at Room Temperature (300 K): $kT=0.02585~{
 m eV}$
- Example 1: Energy Range E_c to $E_c + 3kT$

1. Number of Quantum States in the Conduction Band (N_c)

Energy Range: From E_c to $E_c + 3kT$.

$$E_c + 3kT = E_c + 3 \times 0.02585 \text{ eV} = E_c + 0.07755 \text{ eV}$$

The density of states function $g_c(E)$ for the conduction band is:

$$g_c(E \geq E_c) = rac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c}$$

To find N_c :

$$N_c = \int_{E}^{E_c + 0.07755 \text{ eV}} \frac{4\pi (2m_n^*)^{3/2}}{h^3} \sqrt{E - E_c} \, dE$$

Substitute $x = E - E_{cr}$ so dE = dx:

$$N_c = rac{4\pi (2m_n^*)^{3/2}}{h^3} \int_0^{0.07755 \, \mathrm{eV}} \sqrt{x} \, dx$$

Evaluate the integral:

$$\int_0^{0.07755\,\mathrm{eV}} \sqrt{x}\,dx = rac{2}{3}x^{3/2}igg|_0^{0.07755} = rac{2}{3} imes (0.07755)^{3/2}$$
 $= rac{2}{3} imes (0.07755)^{3/2}$ $= 0.0021$ $= 0.0014\,\mathrm{eV}$

Thus:

$$N_c = rac{4\pi (2m_n^*)^{3/2}}{h^3} imes 0.0014$$

2. Number of Quantum States in the Valence Band (N_v)

Energy Range: From $E_v - 0.07755~{
m eV}$ to E_v .

$$E_v - (E_v - 0.07755 \text{ eV}) = 0.07755 \text{ eV}$$

The density of states function $g_v(E)$ for the valence band is:

$$g_v(E \le E_v) = \frac{4\pi (2m_p^*)^{3/2}}{h^3} \sqrt{E_v - E}$$

To find N_n :

$$N_v = \int_{E_{-0.07755~eV}}^{E_v} \frac{4\pi (2m_p^*)^{3/2}}{h^3} \sqrt{E_v - E} \, dE$$

Substitute $x = E_v - E_t$ so dE = -dx:

$$N_v = \frac{4\pi (2m_p^*)^{3/2}}{h^3} \int_0^{0.07755 \text{ eV}} \sqrt{x} dx$$

The integral result is the same:

$$\int_{0}^{0.07755 \text{ eV}} \sqrt{x} \, dx = 0.0014 \text{ eV}$$

Thus:

$$N_v = \frac{4\pi(2m_p^*)^{3/2}}{h^3} \times 0.0014$$